

# AMENDMENT TRANSMITTAL LETTER

Docket No.  
M4065.0223/P223

Application No.  
09/517,314

Filing Date  
March 2, 2000

Examiner  
D. Kang

Group Art Unit  
2811

Applicant(s): Chih-chen Cho

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Invention: BACKEND METALLIZATION METHOD AND DEVICE OBTAINED THEREFROM

## TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

CLAIMS AS AMENDED					
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	31	- 38 =		x	0.00
Independent Claims	4	- 5 =		x	0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					0.00

☒ Large Entity

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☒ No additional fee is required for this amendment.

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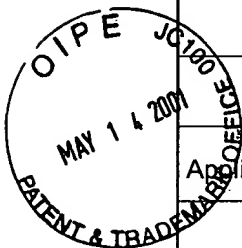
☒ Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.

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Dated: May 14, 2001

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PATENT

Docket No.: M4065.0223/P223

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:  
Chih-chen CHO

Serial No.: 09/517,314

Filed: March 2, 2000

For: BACKEND METALLIZATION  
METHOD AND DEVICE  
OBTAINED THEREFROM

Commissioner for Patents  
Washington, D.C. 20231



Group Art Unit: 2811

Examiner: D. Kang

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AMENDMENT

Dear Sir:

Responsive to the Office action dated February 14, 2001, please amend the above-identified application as follows:

Cancel claims 2 and 19 and non-elected claims 33-38 without prejudice or disclaimer to the subject matter recited therein, amend the paragraph beginning on page 9, line 12 of the specification and claims 1, 9, 17, 18 and 26, and add new claim 39 as follows:

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Page 9, line 12 – page 10, line 2:

a Referring now to FIG. 8, a device constructed in accordance with the invention can be used in a memory circuit, such as a DRAM device 512, or other electronic integrated circuit, within a processor-based system 500. The processor-based system 500 may be a computer system, a process control system or any other system employing a processor and associated memory. The system 500 includes a central processing unit (CPU) 502, which may be a microprocessor. The CPU 502 communicates with the DRAM device 512, which has an array of cells 513 that include the semiconductor device 200 (or the semiconductor device 300), over a bus 516. The CPU 502 further communicates with one or more I/O devices 508, 510 over the bus 516. Although illustrated as a single bus, the bus 516 may be a series of buses and bridges commonly used in a processor-based system. Further components of the system 500 may include a read only memory (ROM) device 514 and peripheral devices such as a floppy disk drive 504, and CD-ROM drive 506. The floppy disk drive 504 and CD-ROM drive 506 communicate with the CPU 502 over the bus 516.

1. (Amended) A semiconductor structure comprising:

- a<sup>2</sup> Sub B<sub>1</sub>
- an insulator layer;
  - a conductive plug positioned within said insulator layer;
  - an etch-stop layer located on said insulator layer and surrounding said plug;
  - a non-conductive layer having an etched via at least partially over said conductive plug; and

a conductive connector formed in said via in electrical contact with said plug  
and including a first conductive layer deposited in and in contact with said etched via and a  
second conductive layer deposited over said first conductive layer, said first conductive layer  
including a portion in contact with said conductive plug.

9. (Amended) The semiconductor structure of claim 1, wherein said first  
conductive layer comprises one or more materials selected from the group consisting of  
aluminum, copper, doped polysilicate, tantalum, tantalum nitride, titanium, titanium  
nitride and tungsten.

17. (Amended) The semiconductor memory device of claim 11, further  
comprising a plurality of said memory cells.

18. (Amended) A semiconductor device comprising:

a conductive element;

an etch-resistant layer surrounding an upper portion of said conductive

element;

a non-conductive layer over said etch resistant layer and having a via over said

conductive element, said via extending down to a level of said conductive element and etch  
resistant layer;

a conductive material located in said via, wherein said conductive material

at end  
Sub 33  
contacts said conductive element; and

a doped region connected to said conductive element.

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a5  
26. (Amended) The processor-based system of claim 25, wherein said conductive connector further comprises a second conductive layer deposited over said first conductive layer.

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to E1  
39. (New) The semiconductor memory device of claim 17, wherein said plurality of said memory cells are in an array.

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